



Improving the Reliability of Next-Generation SSDs using WOM-v codes

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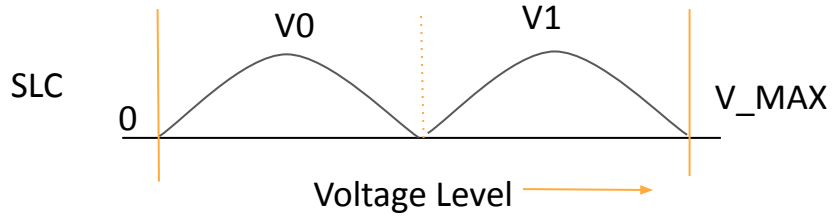
University of Toronto

Bianca Schroeder

University of Toronto

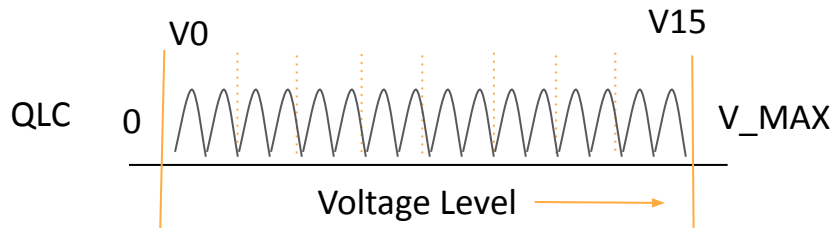
USENIX FAST '22

Motivation

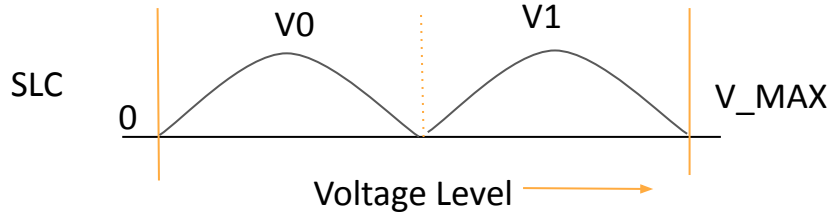


Voltage can only be increased (Program)
Voltage can be reset to zero (Erase)

Increased density – more bits per cell

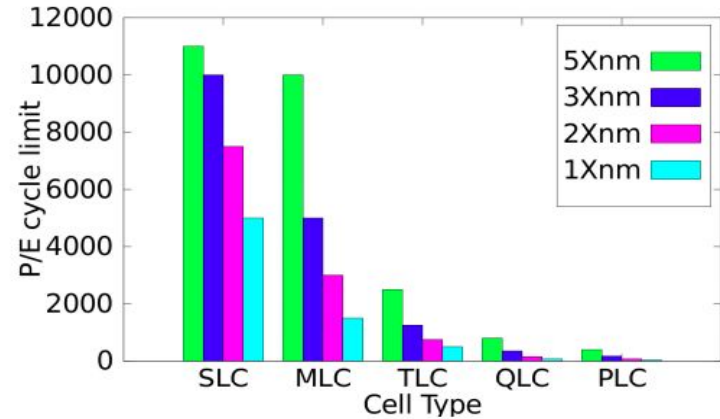
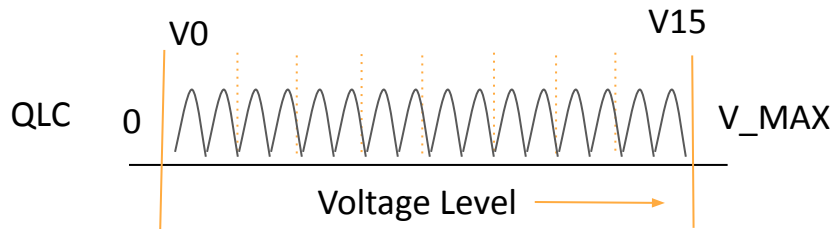


Motivation



Reduced Program and Erase (P/E) cycles

Increased density – more bits per cell



Overwrite between Erase - Write Once Memory Code

HotStorage '20

Rethinking WOM Codes to Enhance the Lifetime in New SSD Generations

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WOM-v Codes

INPUT
DATA

0 1 1 0

1 0 0 1

0 0 1 1

1 1 0 1

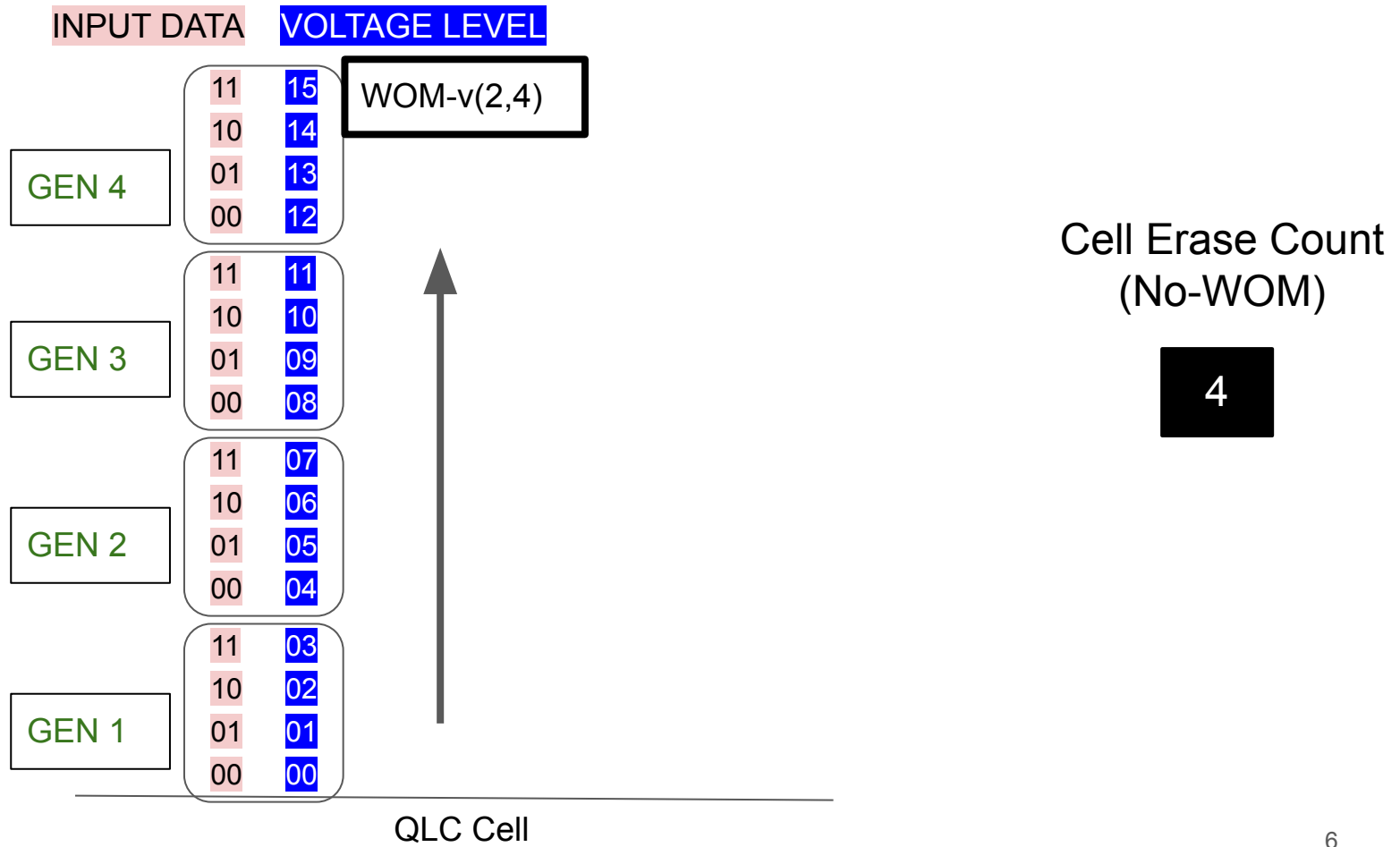


Cell Erase Count
(No-WOM)

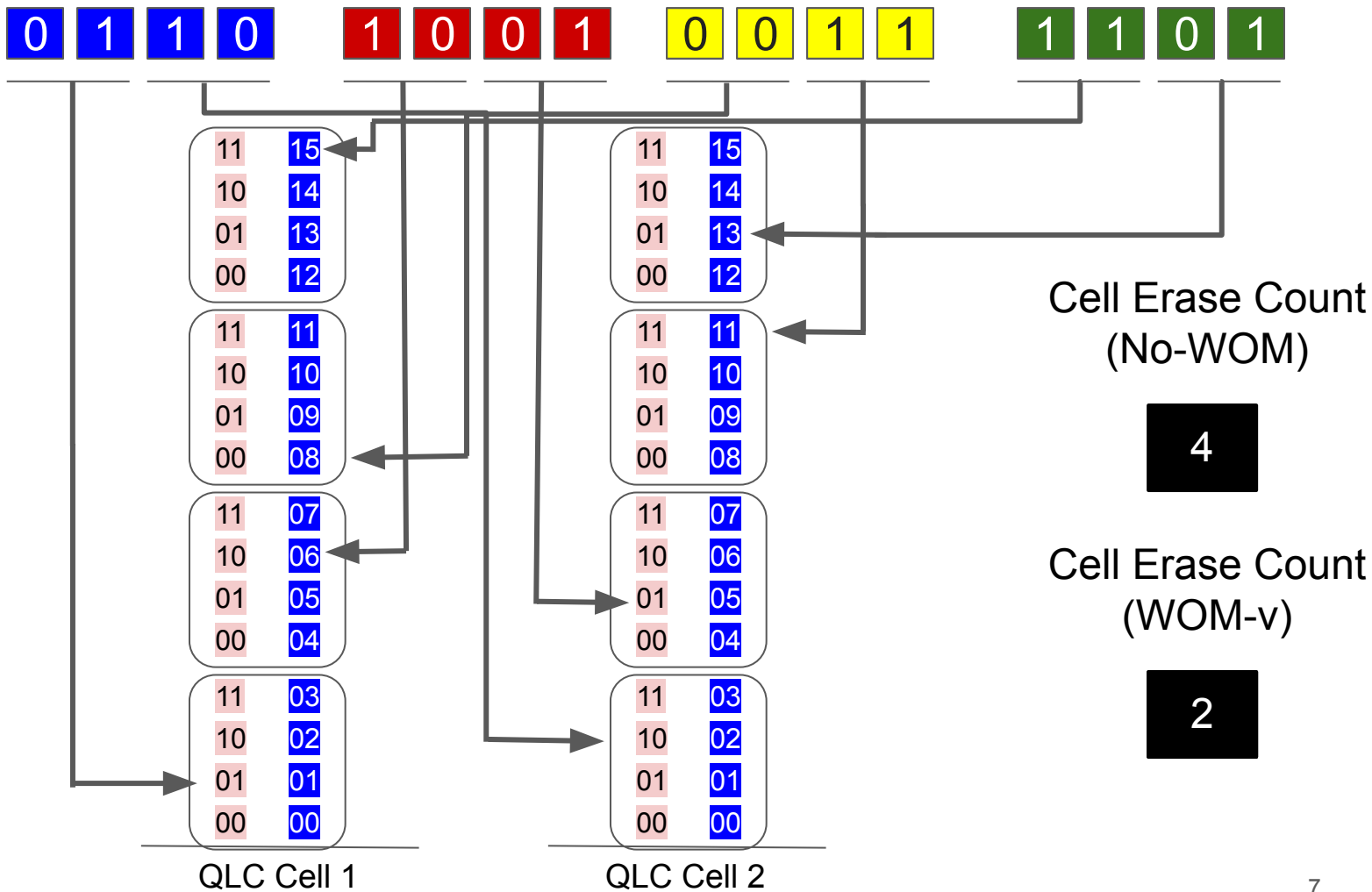
4



QLC Cell



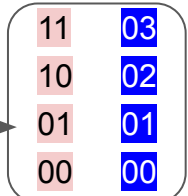
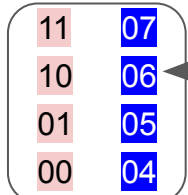
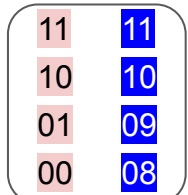
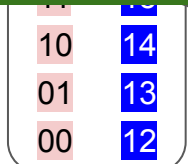
INPUT
DATA



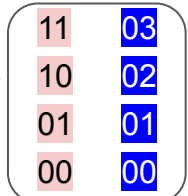
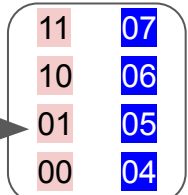
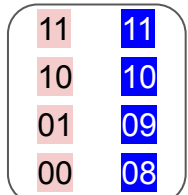
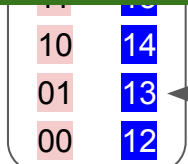
INPUT
DATA

0 1 1 0 1 0 0 1 0 0 1 1 1 1 0 1

WOM-v(2,4) codes reduce erase operation by 2X



QLC Cell 1



QLC Cell 2

Cell Erase Count
(No-WOM)

4

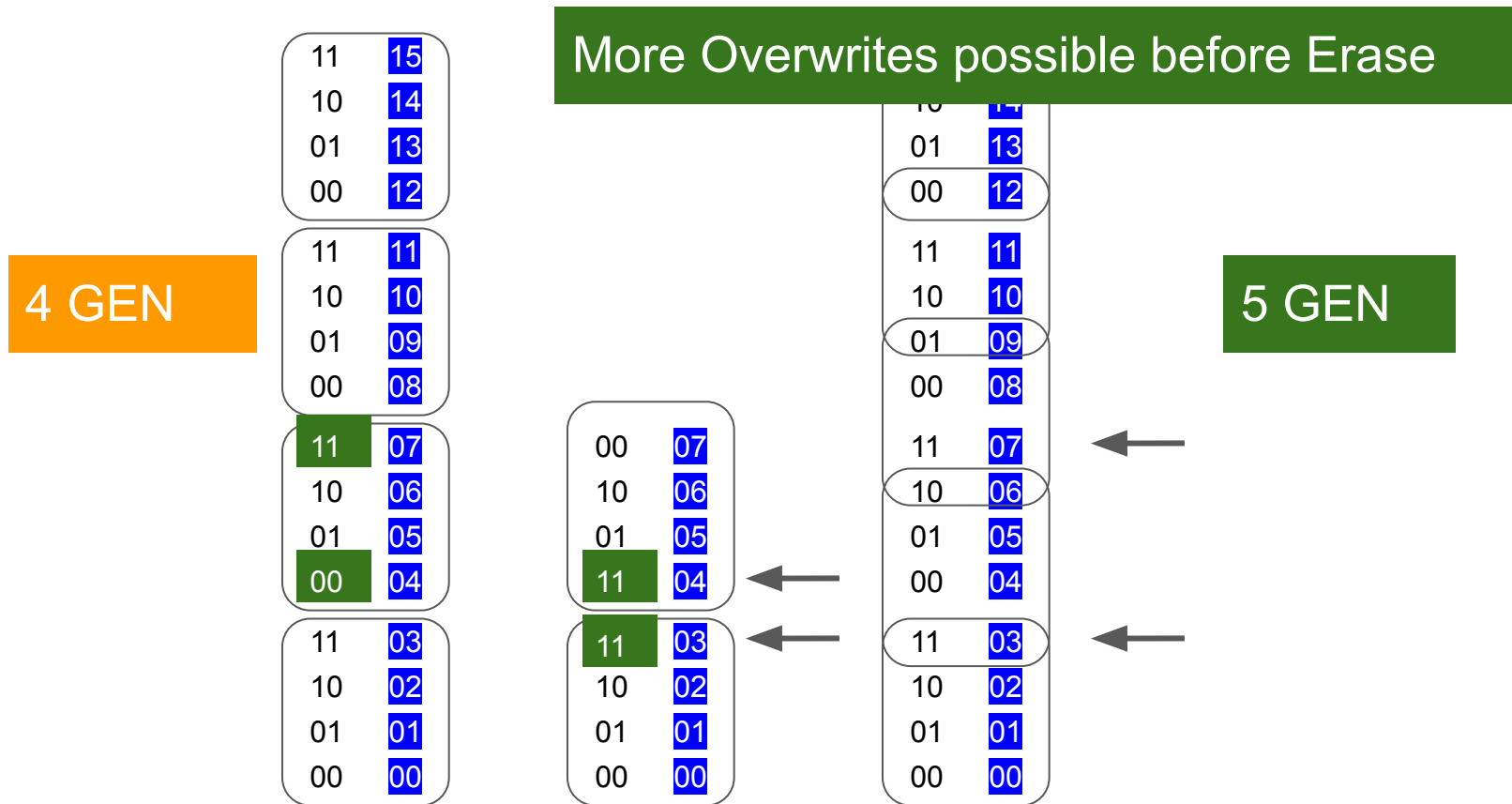
Cell Erase Count
(WOM-v)

2

Optimizations

- Code Word Sharing.
- Same Generation Transition.
- Programming beyond maximum Generations.
- Optimal GC (GC_OPT) Mode.
- No-Read (NR) Mode.

Code Word Sharing



Challenge in introducing WOM-v codes to SSDs

SSD Architecture

Write
Amplification

Performance and
Parallelism

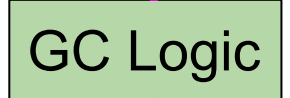
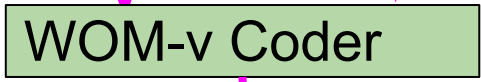
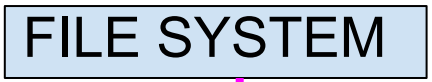
Workload Pattern

Implementation

USERSPACE



KERNEL

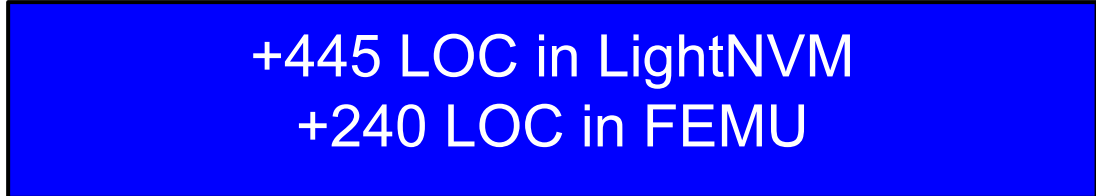


LightNVM Module

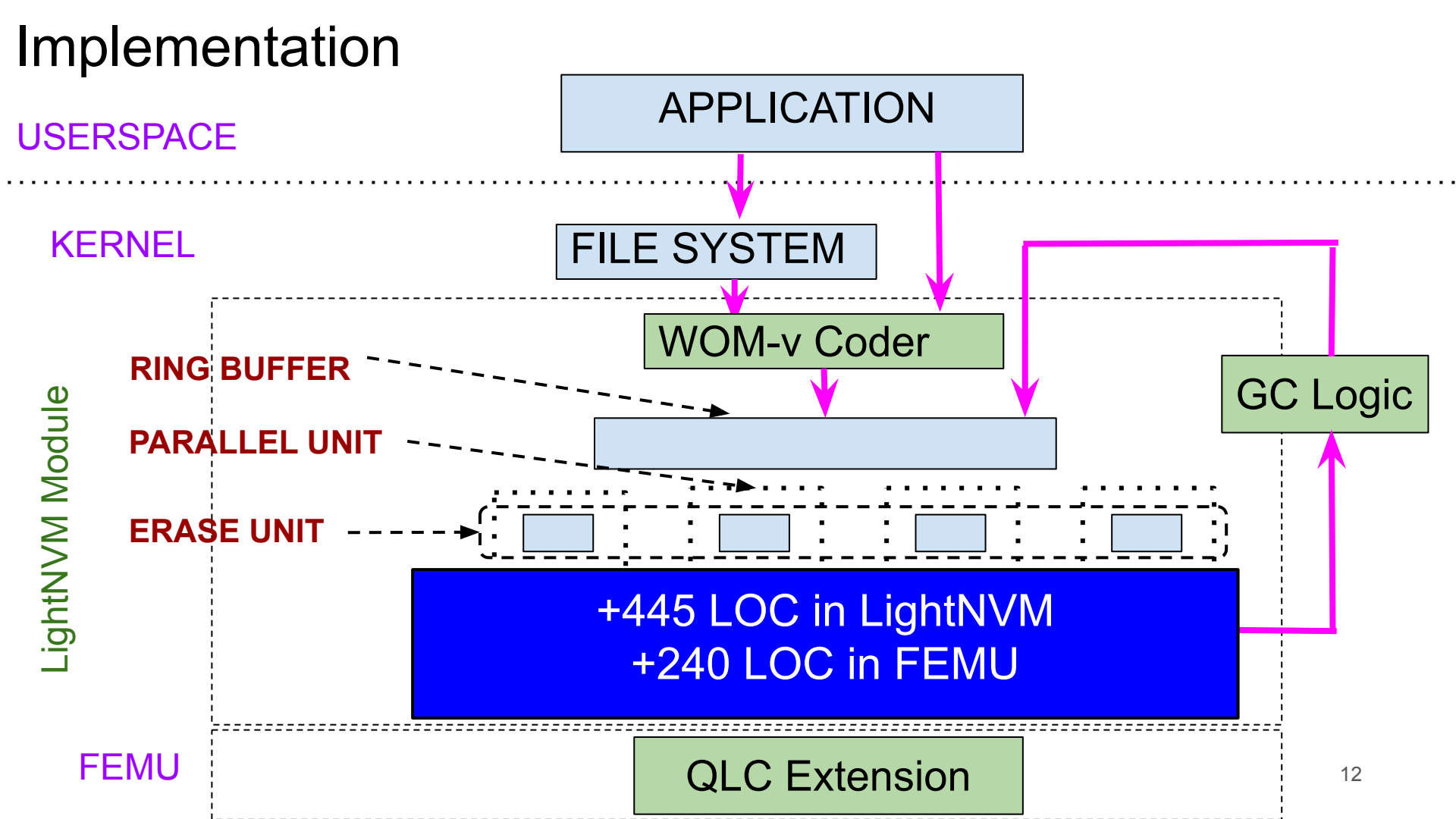
RING BUFFER

PARALLEL UNIT

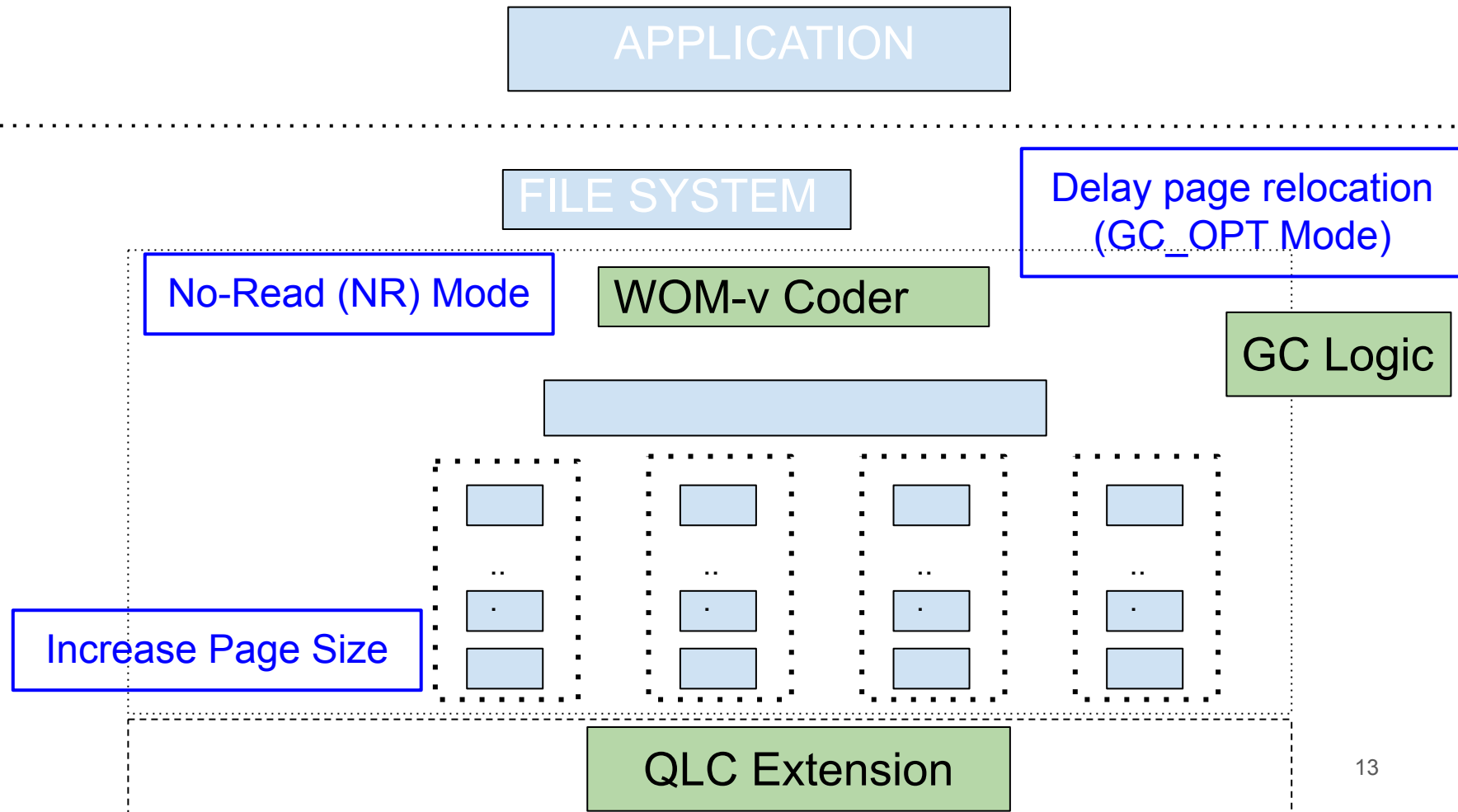
ERASE UNIT



FEMU



Implementation

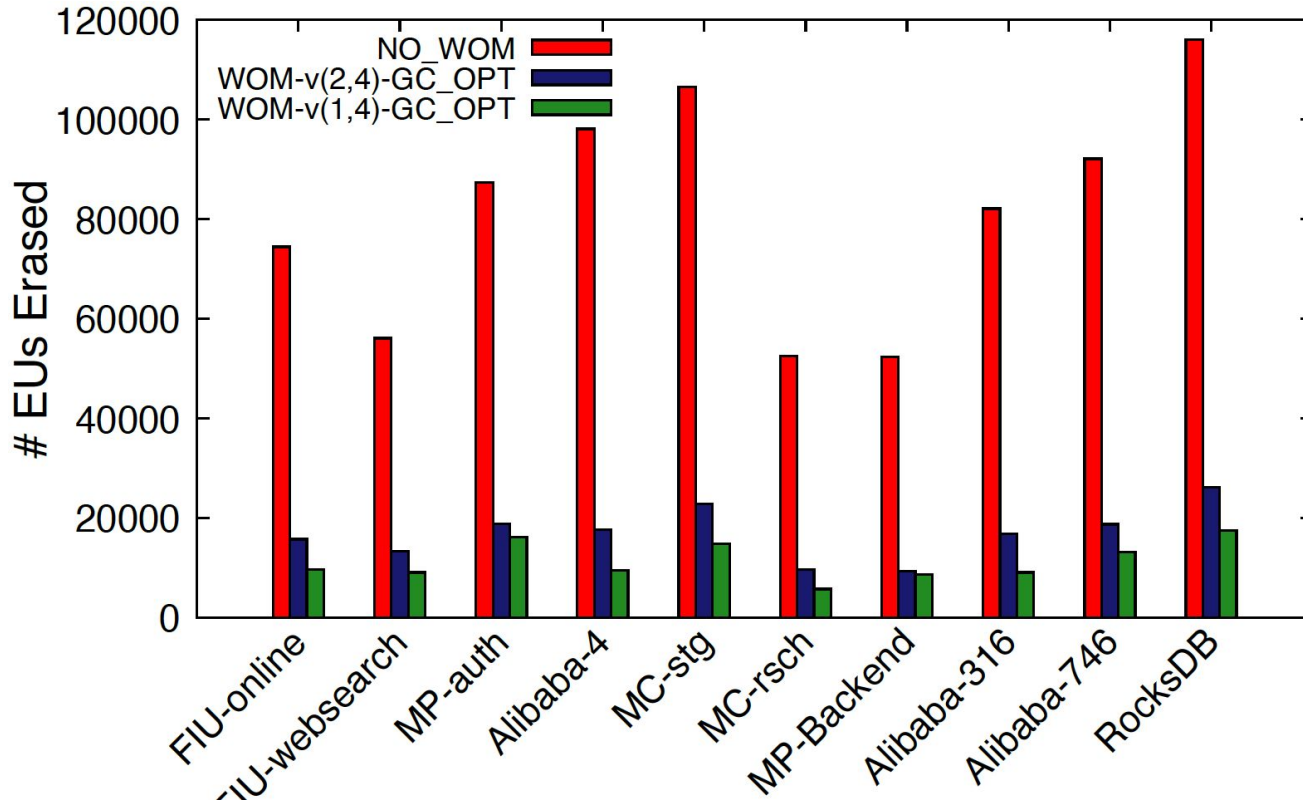


Evaluation: Real World Traces



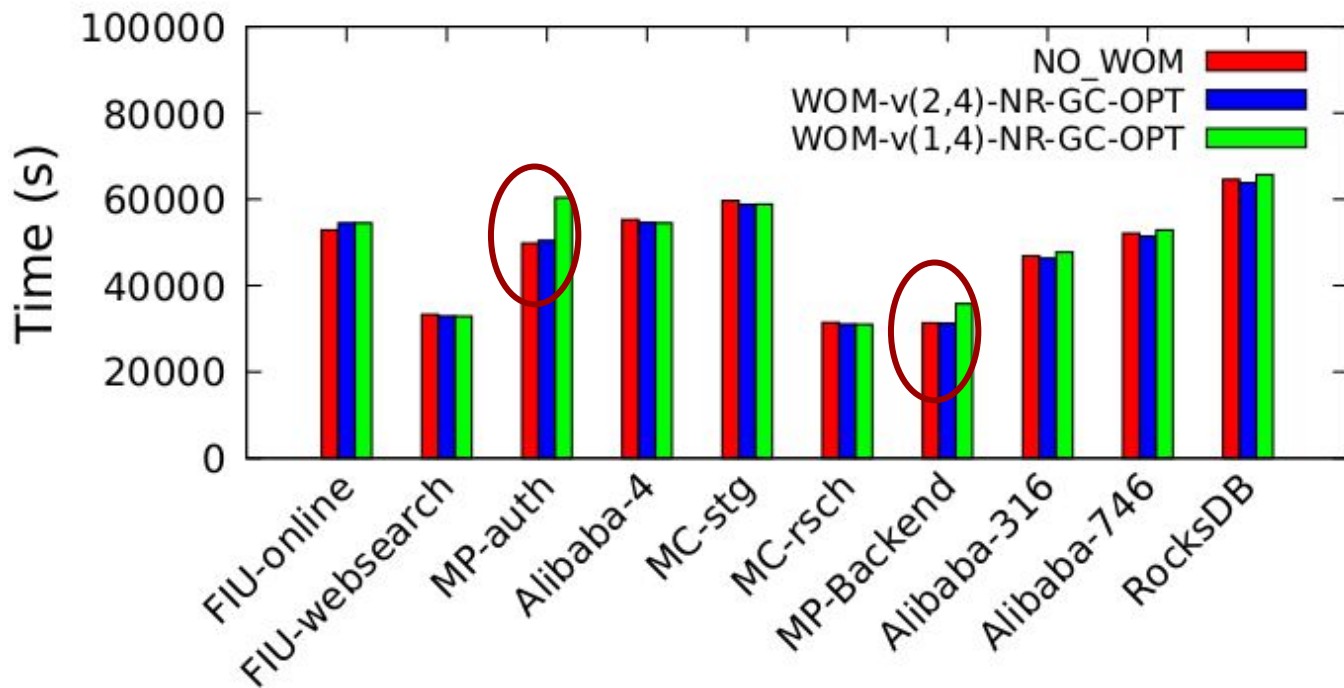
Erase Operation Reduction

4.4 - 11.1x reduction in erase cycles



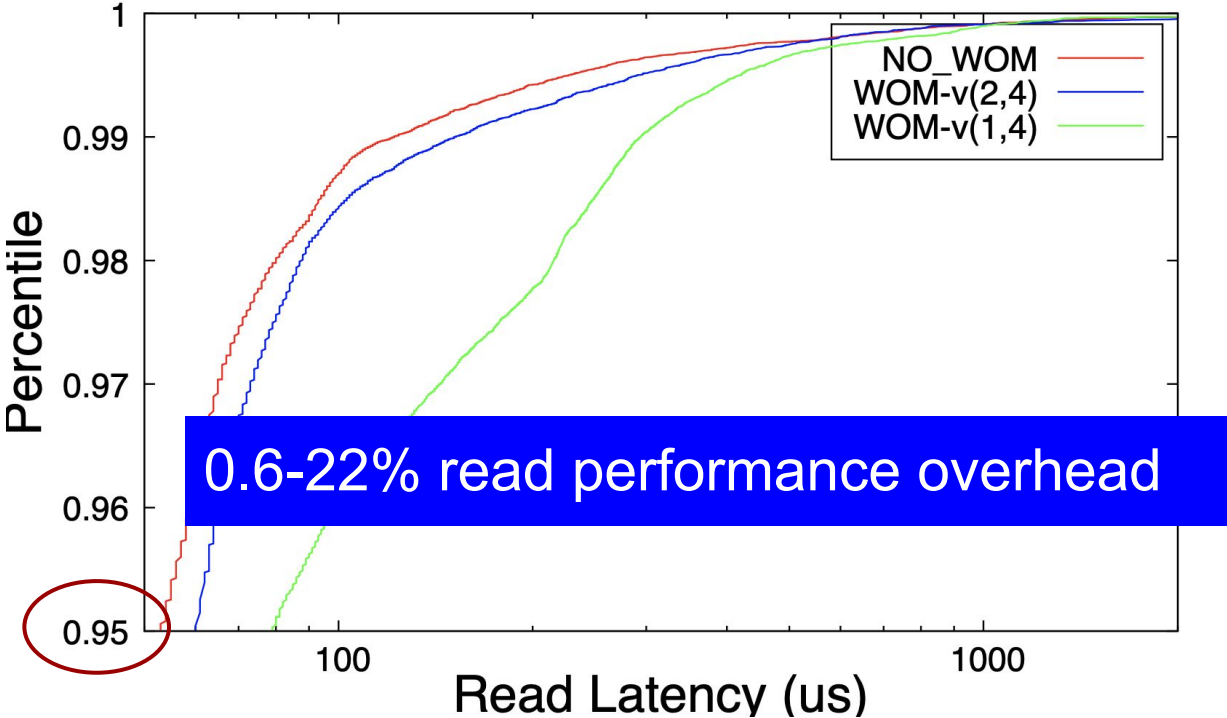
Write Performance

< 8% write performance overhead



Read Performance

Negligible average read latency overhead

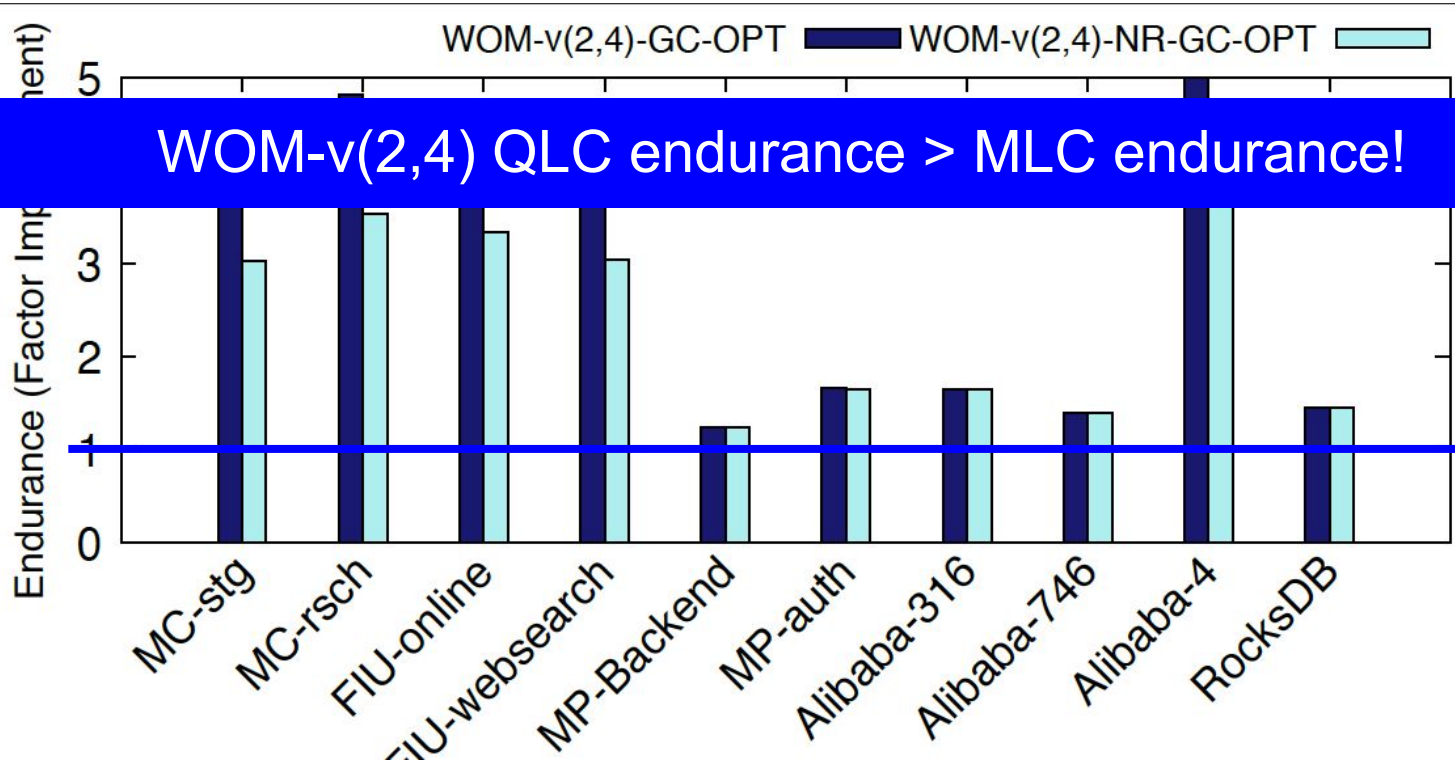


WOM-v(2,4) QLC v/s MLC Drive

- QLC WOM-v(2,4) can store 2 logical bits per cell.
- MLC drives also store 2 logical bits per cell.
- Without WOM-v coding, MLC drive has better endurance than QLC drive.

WOM-v(2,4) QLC v/s MLC endurance?

WOM-v(2,4) QLC v/s MLC Drive




Summary

- **First** design and implementation of **Non-Binary WOM code** for QLC Drives.

- 4.4-11.1x reduced erase operations with minimal performance overheads.

- TLC+QLC FEMU Extension merged upstream with master.



Add TLC-NAND and QLC-NAND Support to FEMU #47

Merged

huaicheng merged 1 commit into `ucare-uchicago:master` from `shehbazj:tlc_qlc_support` on 4 Feb

- WOM-v simulator code <https://github.com/uoftsystems/womv>

Q & A